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IN THE CLAIMS

- 1. (previously presented) A one pot method for large scale production of an organometallic compound comprising a transition metal-containing amide, a transition metal-containing alkoxide, a transition metal-containing diketonate or a transition metal-containing imide, said one pot method_comprising (i) reacting a hydrocarbon or heteroatom-containing material with a base material in the presence of a solvent and under reaction conditions sufficient to produce a first reaction mixture comprising a hydrocarbon or heteroatom-containing compound, (ii) adding a transition metal source compound to said first reaction mixture, (iii) reacting said hydrocarbon or heteroatom-containing compound with said transition metal source compound under reaction conditions sufficient to produce a second reaction mixture comprising said organometallic compound, and (iv) separating said organometallic compound from said second reaction mixture.
- (previously presented) The one pot method of claim 1 wherein the large scale production amounts to about 0.25 kilograms of said organometallic compound.
- 3. (previously presented) The one pot method of claim 1 wherein the large scale production amounts to about 0.5 kilograms of said organometallic compound.
- 4. (previously presented) The one pot method of claim I wherein the large scale production amounts to about 1.0 kilograms of said organometallic compound.

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- 5. (previously presented) The one pot method of claim 1 wherein the organometallic compound yield is from about 75 to 99%.
- 6. (previously presented) The one pot method of claim 1 wherein the organometallic compound yield is from about 80 to 99%.
- 7. (previously presented) The one pot method of claim 1 wherein the hydrocarbon or heteroatom-containing material comprises an amine, alcohol, diketone, imine, hydrocarbon or halogen.
- 8. (original) The one pot method of claim 1 wherein the base material has a pKa greater than about 10.
- 9. (original) The one pot method of claim 1 wherein the base material comprises BuLi, MeLi, NaH, CaH or a lithium amide.
- 10. (previously presented) The one pot method of claim 1 wherein the hydrocarbon or heteroatom-containing compound comprises a lithiated amide, a lithiated_alkoxide, a lithiated_diketonate or a lithiated_imide.
- 11. (previously presented) The one pot method of claim 1 wherein the transition metal source compound is represented by the formula MX_n wherein M is a transition metal, X is halide and n is a value of 3, 4 or 5.
- 12. (original) The one pot method of claim 11 wherein the transition metal is selected from hafnium, titanium, zirconium, tantalum and molybdenum.

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- 13. (previously presented) The one pot method of claim 1 wherein the transition metal source compound comprises HfCl₄, HfF₄, HfBr₄, HfI₄ or Hf(OTf)₄.
- 14. (previously presented) The one pot method of claim 1 wherein the transition metal source compound is HfCl₄.
- 15. (previously presented) The one pot method of claim 1 wherein the transition metal source compound is added to the first reaction mixture at ambient temperature or at a temperature greater than ambient temperature.
- 16. (original) The one pot method of claim 1 wherein the solvent is selected from saturated and unsaturated hydrocarbons, aromatic hydrocarbons, aromatic heterocycles, alkyl halides, silylated hydrocarbons, ethers, polyethers, thioethers, esters, thioesters, lactones, amides, amines, polyamines, nitriles, silicone oils, other aprotic solvents, or mixtures of one or more of the above.
- 17. (original) The one pot method of claim 1 wherein the solvent is selected from hexanes, THF or mixtures thereof.
 - 18. (canceled)
- 19. (currently amended) The one pot method of claim 1 wherein the organometallic compound comprises hafnium amide, hafnium (IV) tert-butoxide, hafnium (IV) acetylacetonate, bis(eyolopontadionyl)hafnium-dichloride-or t-butylimidobis(dimethylamino)hafnium.
- 20. (previously presented) A one pot method for producing a liquid hafnium amide compound comprising (i) reacting an amine with a lithiated base

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material to produce a first reaction mixture comprising a lithium amide, (ii) adding a hashium halide to said first reaction mixture, (iii) reacting said lithium amide with said hafnium halide under reaction conditions sufficient to produce a second reaction mixture comprising said hafnium amide compound, and (iv) separating said hafnium amide compound from said second reaction mixture.

- (previously presented) A one pot method for large scale production of 21. an organometallic compound comprising a transition metal-containing amide, a transition metal-containing alkoxide, a transition metal-containing diketonate, a transition metal-containing cyclopentadienide or a transition metal-containing imide, said one pot method comprising (i) reacting a hydrocarbon or heteroatom-containing material with a base material in the presence of a solvent and under reaction conditions sufficient to produce a first reaction mixture comprising a hydrocarbon or heteroatom-containing compound, (ii) adding a transition metal source compound to said first reaction mixture, wherein said transition metal source compound is added to said first reaction mixture at ambient temperature or at a temperature greater than ambient temperature, (iii) reacting said hydrocarbon or heteroatom-containing compound with said transition metal source compound under reaction conditions sufficient to produce a second reaction mixture comprising said organometallic compound, and (iv) separating said organometallic compound from said second reaction mixture.
- (previously presented) A one pot method for large scale production of 22. an organometallic compound comprising a transition metal-containing amide, a transition metal-containing alkoxide, a transition metal-containing diketonate, a transition metal-containing cyclopentadienide or a transition metal-containing imide, said one pot method comprising (i) reacting a hydrocarbon or heteroatom-containing material with a base material in the presence of a solvent and under reaction

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conditions sufficient to produce a first reaction mixture comprising a hydrocarbon or heteroatom-containing compound, (ii) adding a transition metal source compound to said first reaction mixture, (iii) reacting said hydrocarbon or heteroatom-containing compound with said transition metal source compound under reaction conditions sufficient to produce a second reaction mixture comprising said organometallic compound, and (iv) separating said organometallic compound from said second reaction mixture; wherein the organometallic compound yield is from about 80 to 99%.

- an organometallic compound comprising (i) reacting a hydrocarbon or heteroatom-containing material with a base material in the presence of a solvent and under reaction conditions sufficient to produce a first reaction mixture comprising a hydrocarbon or heteroatom-containing compound, wherein said solvent is selected from hexanes, THF or mixtures thereof, (ii) adding a metal source compound to said first reaction mixture, (iii) reacting said hydrocarbon or heteroatom-containing compound with said metal source compound under reaction conditions sufficient to produce a second reaction mixture comprising said organometallic compound, and (iv) separating said organometallic compound from said second reaction mixture.
- 24. (new) The one pot method of claim 21 wherein the large scale production amounts to about 0.25 kilograms of said organometallic compound.
- 25. (new) The one pot method of claim 21 wherein the large scale production amounts to about 0.5 kilograms of said organometallic compound.
- 26. (new) The one pot method of claim 21 wherein the large scale production amounts to about 1.0 kilograms of said organometallic compound.

- 27. (new) The one pot method of claim 21 wherein the organometallic compound yield is from about 75 to 99%.
- 28. (new) The one pot method of claim 21 wherein the organometallic compound yield is from about 80 to 99%.
- 29. (new) The one pot method of claim 21 wherein the hydrocarbon or heteroatom-containing material comprises an amine, alcohol, diketone, cyclopentadiene, imine, hydrocarbon or halogen.
- 30. (new) The one pot method of claim 21 wherein the base material has a pKa greater than about 10.
- 31. (new) The one pot method of claim 21 wherein the base material comprises BuLi, MeLi, NaH, CaH or a lithium amide.
- 32. (new) The one pot method of claim 21 wherein the hydrocarbon or heteroatom-containing compound comprises a lithiated amide, a lithiated_alkoxide, a lithiated_diketonate, lithiated cyclopentadienide or a lithiated_imide.
- 33. (new) The one pot method of claim 21 wherein the transition metal source compound is represented by the formula MX_n wherein M is a transition metal, X is halide and n is a value of 3, 4 or 5.
- 34. (new) The one pot method of claim 33 wherein the transition metal is selected from hafnium, titanium, zirconium, tantalum and molybdenum.

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- 35. (new) The one pot method of claim 21 wherein the transition metal source compound comprises HfCl₄, HfF₄, HfBr₄, HfI₄ or Hf(OTf)₄.
- 36. (new) The one pot method of claim 21 wherein the solvent is selected from saturated and unsaturated hydrocarbons, aromatic hydrocarbons, aromatic heterocycles, alkyl halides, silylated hydrocarbons, ethers, polyethers, thioethers, esters, thioesters, lactones, amides, amines, polyamines, nitriles, silicone oils, other aprotic solvents, or mixtures of one or more of the above.
- 37. (new) The one pot method of claim 21 wherein the organometallic compound comprises hafnium amide, hafnium (IV) tert-butoxide, hafnium (IV) acetylacetonate, bis(cyclopentadienyl)hafnium dichloride or t-butylimidobis(dimethylamino)hafnium.
- 38. (new) The one pot method of claim 22 wherein the large scale production amounts to about 0.25 kilograms of said organometallic compound.
- 39. (new) The one pot method of claim 22 wherein the large scale production amounts to about 0.5 kilograms of said organometallic compound.
- 40. (new) The one pot method of claim 22 wherein the large scale production amounts to about 1.0 kilograms of said organometallic compound.
- 41. (new) The one pot method of claim 22 wherein the hydrocarbon or heteroatom-containing material comprises an amine, alcohol, diketone, cyclopentadiene, imine, hydrocarbon or halogen.

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- 42. (new) The one pot method of claim 22 wherein the base material has a pKa greater than about 10.
- 43. (new) The one pot method of claim 22 wherein the base material comprises BuLi, MeLi, NaH, CaH or a lithium amide.
- 44. (new) The one pot method of claim 22 wherein the hydrocarbon or heteroatom-containing compound comprises a lithiated amide, a lithiated_alkoxide, a lithiated_diketonate, lithiated cyclopentadienide or a lithiated_imide.
- 45. (new) The one pot method of claim 22 wherein the transition metal source compound is represented by the formula MX_n wherein M is a transition metal, X is halide and n is a value of 3, 4 or 5.
- 46. (new) The one pot method of claim 45 wherein the transition metal is selected from hafnium, titanium, zirconium, tantalum and molybdenum.
- 47. (new) The one pot method of claim 22 wherein the transition metal source compound comprises HfCl₄, HfF₄, HfBr₄, HfI₄ or Hf(OTf)₄.
- 48. (new) The one pot method of claim 22 wherein the transition metal source compound is added to the first reaction mixture at ambient temperature or at a temperature greater than ambient temperature.
- 49. (new) The one pot method of claim 22 wherein the solvent is selected from saturated and unsaturated hydrocarbons, aromatic hydrocarbons, aromatic heterocycles, alkyl halides, silylated hydrocarbons, ethers, polyethers, thioethers,

esters, thioesters, lactones, amides, amines, polyamines, nitriles, silicone oils, other aprotic solvents, or mixtures of one or more of the above.

- 50. (new) The one pot method of claim 22 wherein the organometallic compound comprises hafnium amide, hafnium (IV) tert-butoxide, hafnium (IV) acetylacetonate, bis(cyclopentadienyl)hafnium dichloride or t-butylimidobis(dimethylamino)hafnium.
- 51. (new) The one pot method of claim 23 wherein the large scale production amounts to about 0.25 kilograms of said organometallic compound.
- 52. (new) The one pot method of claim 23 wherein the large scale production amounts to about 0.5 kilograms of said organometallic compound.
- 53. (new) The one pot method of claim 23 wherein the large scale production amounts to about 1.0 kilograms of said organometallic compound.
- 54. (new) The one pot method of claim 23 wherein the organometallic compound yield is from about 75 to 99%.
- 55. (new) The one pot method of claim 23 wherein the organometallic compound yield is from about 80 to 99%.
- 56. (new) The one pot method of claim 23 wherein the hydrocarbon or heteroatom-containing material comprises an amine, alcohol, diketone, cyclopentadiene, imine, hydrocarbon or halogen.

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- 57. (new) The one pot method of claim 23 wherein the base material has a pKa greater than about 10.
- 58. (new) The one pot method of claim 23 wherein the base material comprises BuLi, MeLi, NaH, CaH or a lithium amide.
- 59. (new) The one pot method of claim 23 wherein the hydrocarbon or heteroatom-containing compound comprises a lithiated amide, a lithiated alkoxide, a lithiated diketonate, lithiated cyclopentadienide or a lithiated imide.
- 60. (new) The one pot method of claim 23 wherein the transition metal source compound is represented by the formula MX_n wherein M is a transition metal, X is halide and n is a value of 3, 4 or 5.
- 61. (new) The one pot method of claim 60 wherein the transition metal is selected from hafnium, titanium, zirconium, tantalum and molybdenum.
- 62. (new) The one pot method of claim 23 wherein the transition metal source compound comprises HfCl₄, HfF₄, HfBr₄, Hfl₄ or Hf(OTf)₄.
- 63. (new) The one pot method of claim 23 wherein the transition metal source compound is added to the first reaction mixture at ambient temperature or at a temperature greater than ambient temperature.
- 64. (new) The one pot method of claim 23 wherein the organometallic compound comprises hafnium amide, hafnium (IV) tert-butoxide, hafnium (IV) acetylacetonate, bis(cyclopentadienyl)hafnium dichloride or t-butylimidobis(dimethylamino)hafnium.